

L Number	Hits	Search Text	DB	Time stamp
1	11	"semiconductor memory device" and ("first region" near2 "first direction")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:57
2	10	("semiconductor memory device" and ("first region" near2 "first direction")) and "second region"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:42
5	20	"word line" and ("first region" near2 "first direction")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:46
7	19	("word line" and ("first region" near2 "first direction")) and select\$8	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:47
8	12	((("word line" and ("first region" near2 "first direction")) and select\$8) and activat\$8	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:47
9	9	((("word line" and ("first region" near2 "first direction")) and select\$8) and activat\$8) and "sense amplifier"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:57
10	346	"semiconductor memory device" and "open bit line"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:58
11	16	("semiconductor memory device" and "open bit line") and "first region"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:58
12	61	("semiconductor memory device" and "open bit line") and "first direction"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:58
13	55	("semiconductor memory device" and "open bit line") and "second direction"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:58
14	16	("semiconductor memory device" and "open bit line") and "second region"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:58
15	8	((("semiconductor memory device" and "open bit line") and "second region") and perpendicular	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:59
16	2	((("semiconductor memory device" and "open bit line") and "first region") and ("semiconductor memory device" and "open bit line") and "first direction") and ((("semiconductor memory device" and "open bit line") and "second direction") and ((("semiconductor memory device" and "open bit line") and "second region") and ((("semiconductor memory device" and "open bit line") and "second region") and perpendicular	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:59
-	1	"20040017716"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:05
-	4	((("6639822") or ("6545897") or ("6373776") or ("6370054")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 01:56
-	5	((("6639822") or ("6545897") or ("6373776") or ("6370054")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:02

-	2	"20030112695"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 01:58
-	2	"20010009519"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:00
-	2	"20020080640"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:01
-	5	"20040017716" or "20030112695" or "20010009519" or "20020080640"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:01
-	9	("20040017716" or "20030112695" or "20010009519" or "20020080640") or (("6639822") or ("6545897") or ("6373776") or ("6370054")).PN.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:02
-	37122	"semiconductor memory device"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:06
-	17	"semiconductor memory device" and ("first region" near4 "first direction")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/22 16:41
-	47	"semiconductor memory device" and first adj2 region adj6 first adj2 direction	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:09
-	41	("semiconductor memory device" and first adj2 region adj6 first adj2 direction) and second adj2 direction	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:10
-	210	"semiconductor memory device" and "second direction perpendicular" near3 "first direction"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:11
-	209	"semiconductor memory device" and "second direction perpendicular" adj3 "first direction"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:13
-	1	"semiconductor memory device" and "selected first region"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:14
-	42	"semiconductor memory device" and select\$6 adj2 first adj2 region	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:14
-	19	("semiconductor memory device" and select\$6 adj2 first adj2 region) and select\$6 adj2 second adj2 region	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/20 02:15
-	19	("semiconductor memory device" and select\$6 adj2 first adj2 region) and select\$6 adj2 second adj2 region	USPAT; US-PGPUB	2004/02/20 02:15
-	13	("semiconductor memory device" and select\$6 adj2 first adj2 region) and select\$6 adj2 second adj2 region	USPAT	2004/02/20 02:15
-	6	"semiconductor memory device" and select\$6 adj2 first adj2 region) and select\$6 adj2 second adj2 region	US-PGPUB	2004/02/20 03:02